UTC 2SD1060 NPN EPITAXIAL PLANAR TRANSISTOR

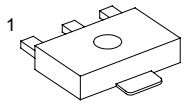
NPN EPITAXIAL PLANAR SILICON TRANSISTOR

FEATURE

*Low collector-to-emitter saturation voltage:
$V_{CE(sat)}$=0.4V max/I_C=3A, I_B=0.3A

APPLICATIONS

*Suitable for relay drivers, high-speed inverter, converters, and other general large-current switching.



SOT-89

1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current	IC	5	A
Collector Current (Pulse)	I_{CP}	9	A
Collector Dissipation	P_C	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	I_{CBO}	V_{CB}=40V,I_E=0			0.1	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4V,I_C=0			0.1	mA
DC Current Gain	hFE1 hFE2	V_{CE}=2V, I_C=1A V_{CE}=2V, I_C=3A,	70 30		360	
Gain bandwidth product	fT	V_{CE} =5V, I_C =1A		30		MHZ
Output Capacitance	Cob	V_{CB} =10V, f=1MHz		100		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C =3A, I_B =0.3A			0.4	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C =1mA, I_E =0	60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C =1mA, R_{BE} =∞	50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_C =0, I_E =1mA	6			V
Turn-ON Time	tON	See specified test circuit		0.1		μs
Storage Time	tstg	See specified test circuit		1.4		μs
Fall Time	tf	See specified test circuit		0.2		μs

CLASSIFICATION of hFE1

RANK	Q	R	S
RANGE	70-140	100-200	180-360

SWITCHING TIME TEST CIRCUIT